

UNISONIC TECHNOLOGIES CO., LTD

100N02

Power MOSFET

100A, 15V N-CHANNEL POWER TRENCH MOSFET

DESCRIPTION

The UTC 100N02 is an N-channel Power Trench MOSFET, it uses UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and high switching speed.

The UTC 100N02 is generally applied in synchronous Rectification or DC to DC convertor.

FEATURES

* $R_{DS(ON)}$ <12m Ω @ V_{GS}=4.5V, I_D =55A

- $R_{DS(ON)}$ <17m Ω @ V_{GS}=3.5V, I_D =30A
- * Low Gate Charge (Typical 46nC)
- * High Switching Speed
- * High Power and Current Handling Capability

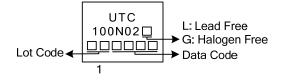
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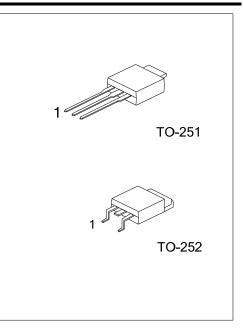
ORDERING INFORMATION									
Ordering Number		Deekere	Pin Assignment			Dealving			
Lead Free	Halogen Free	Package	1	2	3	Packing			
100N02L-TM3-T	100N02G-TM3-T	TO-251	G	D	S	Tube			
100N02L-TN3-R	100N02G-TN3-R	TO-252	G	D	S	Tape Reel			

Note: Pin Assignment: G: Gate D: Drain S: Source

100N02L-TN3-R	(1) R: Tape Reel, T: Tube
(2)Package Type	(2) TN3: TO-252, TM3: TO-251
(3)Green Package	(3) L: Lead Free, G: Halogen Free and Lead Free

MARKING





ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	15	V	
Gate-Source Voltage		V _{GSS}	±8	V	
Drain Current	Continuous	ID	100	А	
Drain Current	Pulsed	I _{DM}	400	А	
Avalanche Energy	Single Pulsed	E _{AS}	12	mJ	
Power Dissipation Junction Temperature Storage Temperature Range		PD	54	W	
		TJ	+150	°C	
		T _{STG}	-55~+150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	62.5	°C/W	
Junction to Case	θ _{JC}	2.3	°C/W	

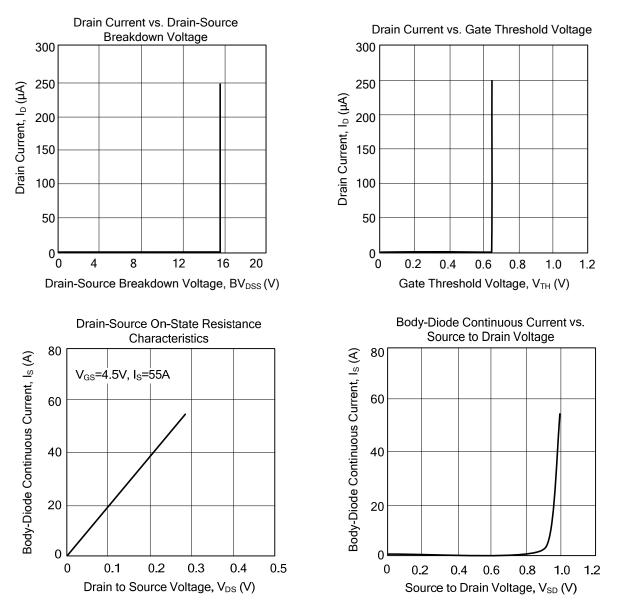
ELECTRICAL CHARACTERISTICS

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PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS			1				
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	15			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =15V			1	μA
Gate-Source Leakage Current	Forward	- I _{GSS}	V _{GS} =+8V			±100	nA
	Reverse		V _{GS} =-8V			±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	I _D =250μA	0.5		1.2	V
Static Drain Source On State Re	eistanco		V _{GS} =4.5V, I _D =55A			12	mΩ
Static Drain-Source On-State Resista		$R_{DS(ON)}$	V _{GS} =3.5V, I _D =30A			17	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}			3565		рF
Output Capacitance Reverse Transfer Capacitance		Coss	V _{GS} =0V, V _{DS} =20V, f=1.0MHz		1310		рF
		C _{RSS}			395		рF
SWITCHING PARAMETERS					_	_	
Total Gate Charge		Q_{G}			46	60	nC
Gate to Source Charge		Q_{GS}	−V _{GS} =10V, V _{DD} =12V, I _D =0.3A, −I _G =100µA		6.9		nC
Gate to Drain Charge		Q_{GD}	-ισ-ισομΑ		9.8		nC
Turn-ON Delay Time		t _{D(ON)}			9		ns
Rise Time		t _R	V _{DD} =10V, I _D =0.16A, R _G =25Ω,		106		ns
Turn-OFF Delay Time		t _{D(OFF)}	V _{GS} =0~10V		53		ns
Fall-Time		t _F			41		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Vol	tage	V _{SD}	I _S =55A			1.3	V



100N02

TYPICAL CHARACTERISTICS



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